TOSHIBA Transistor Silicon NPN Epitaxial Type

2SC5819

High-Speed Switching Applications DC-DC Converter Applications

• High DC current gain: $h_{FE} = 400$ to 1000 (IC = 0.15 A)

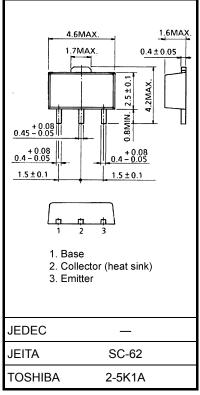
Absolute Maximum Ratings (Ta = 25°C)

- Low collector-emitter saturation voltage: V_{CE} (sat) = 0.12 V (max)
- High-speed switching: $t_f = 45 \text{ ns}$ (typ.)

Symbol Rating Unit Characteristics Collector-base voltage V_{CBO} 40 V 30 V Collector-emitter voltage VCEX 20 V Collector-emitter voltage VCEO Emitter-base voltage 7 V VEBO DC IC 1.5 Collector current А Pulse 2.5 ICP 150 Base current I_{B} mΑ 2.0 t = 10 s Collector power w P_C (Note 1) dissipation DC 1.0 Junction temperature Тj 150 °C °C Storage temperature range Tstg -55 to 150



Unit: mm



Weight: 0.05 g (typ.)

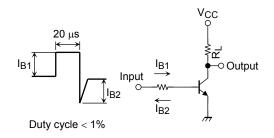
Note 1: Mounted on an FR4 board (glass epoxy, 1.6 mm thick, Cu area: 645 mm²)

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

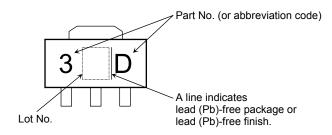
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current		I _{CBO}	$V_{CB}=40~V,~I_{E}=0$			100	nA
Emitter cut-off current		I _{EBO}	$V_{EB} = 7 V, I_{C} = 0$	_	_	100	nA
Collector-emitter breakdown voltage		V (BR) CEO	$I_{C} = 10 \text{ mA}, I_{B} = 0$	20	_	_	V
DC current gain		h _{FE} (1)	$V_{CE} = 2 V, I_C = 0.15 A$	400		1000	
		h _{FE} (2)	$V_{CE} = 2 V, I_C = 0.5 A$	200			
Collector-emitter saturation voltage		V _{CE (sat)}	$I_{C} = 0.5 \text{ A}, I_{B} = 10 \text{ mA}$			0.12	V
Base-emitter saturation voltage		V _{BE (sat)}	$I_{C} = 0.5 \text{ A}, I_{B} = 10 \text{ mA}$	_	_	1.10	V
Collector output capacitance		C _{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	_	18	_	pF
Switching time	Rise time	tr	See Figure 1.		43		
	Storage time	t _{stg}	$V_{CC} \simeq 12 \text{ V}, \text{ R}_L = 24 \Omega$	—	295	—	ns
	Fall time	t _f	$I_{B1} = -I_{B2} = 17 \text{ mA}$		45		

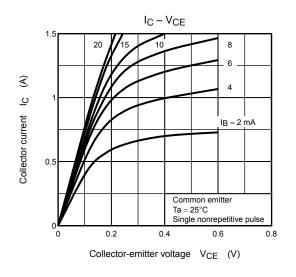


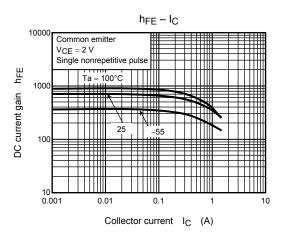


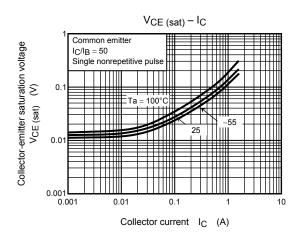
Marking

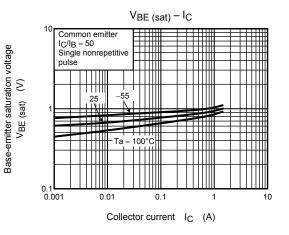


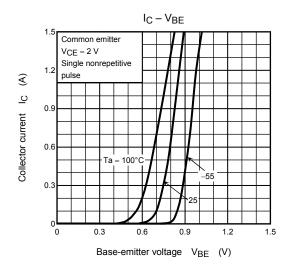
TOSHIBA

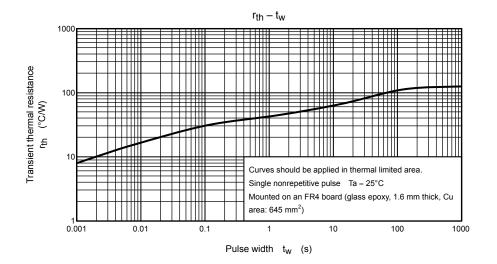


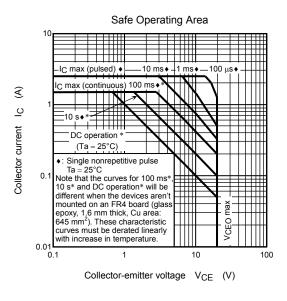












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